

L Number	Hit Number	Text	DB	Time stamp
1		"DRAM or "dynamic random access memory"';.PN.	USPAT;	2003/01/16
2	43754	DRAM or "dynamic random access memory"	EPO; JPO;	13:54
3	19097	cobalt or Co; same (HCl or hydrochloric acid or "hydrogen peroxide" or "H <sub>2</sub> O <sub>2</sub> .sub.2")	IBM_TDB	2003/01/16
4	97	DRAM or "dynamic random access memory") and (cobalt or Co) same (HCl or hydrochloric acid or "hydrogen peroxide" or "H <sub>2</sub> O <sub>2</sub> .sub.2")	USPAT;	2003/01/16
11	87	cobalt or Co; same (HCl or hydrochloric acid or "hydrogen peroxide" or "H <sub>2</sub> O <sub>2</sub> .sub.2") same (silicide or (silicide or same (heat\$5 or anneal\$4 or sinter\$4	EPO; JPO;	14:00
12	137	cobalt or Co and HCl or hydrochloric acid or "hydrogen peroxide" or "H <sub>2</sub> O <sub>2</sub> .sub.2") and (silicide or silicide or same (heat\$5 or anneal\$4 or sinter\$4	IBM_TDB	2003/01/16
13	1101	cobalt or Co and (HCl or hydrochloric acid or "hydrogen peroxide" or "H <sub>2</sub> O <sub>2</sub> .sub.2") and (silicide or silicide or same (heat\$5 or anneal\$4 or sinter\$4) and etch\$4	USPAT;	2003/01/16
14	62	cobalt or Co and (HCl or hydrochloric acid or "hydrogen peroxide" or "H <sub>2</sub> O <sub>2</sub> .sub.2") and (silicide or silicide or same (heat\$5 or anneal\$4 or sinter\$4) and etch\$4 and 418/.ccis. and etch\$3 same cobalt or Co same (etch\$3 or remove\$3	EPO; JPO;	15:14
15	239	unrelated same (cobalt or Co; same (heat\$3 or remove\$3) and (DRAM or "dynamic random access memory")	IBM_TDB	2003/01/16
16	239	unrelated same (cobalt or Co; same (heat\$3 or remove\$3) and (DRAM or "dynamic random access memory")	USPAT;	2003/01/16
17	97	unrelated same (cobalt or Co; same (heat\$3 or remove\$3) and (DRAM or "dynamic random access memory")	EPO; JPO;	15:40
			IBM_TIB	2003/01/16
			USPAT;	15:41
			EPO; JPO;	IBM_TIB